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Sheet 1 of 1

Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 127516 <div style="font-size: 24pt; font-weight: bold; text-align: center;">10/ 573 822</div>		APPLICATION NO. New U.S. National Stage of PCT/JP2004/015395	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Ryoji HOSHI et al.			
				FILING DATE March 28, 2006			
U.S. PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Name			
/G.N.R./	1.	US 2002/0017234 A1	02/14/2002	ONO et al.			
FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation	
/G.N.R./	2.	JP-A-07-223893	08/22/1995	JAPAN	X	X	
/G.N.R./	3.	JP-A-08-157293	06/18/1996	JAPAN	X	X	
/G.N.R./	4.	JP-A-11-043397	02/16/1999	JAPAN	X	X	
/G.N.R./	5.	JP-A-2002-012498	01/15/2002	JAPAN	X	X	
/G.N.R./	6.	JP-A-2002-226296	08/14/2002	JAPAN	X	X	
/G.N.R./	7.	JP-A-08-330316	12/13/1996	JAPAN	X	X	
/G.N.R./	8.	JP-A-11-079889	03/23/1999	JAPAN	X	X	
OTHER DOCUMENTS							
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)					
/G.N.R./	9.	D.T.J. HURLE et al.; "Mechanism of Swirl Defects Formation in Silicon"; <i>Journal of Crystal Growth</i> ; Vol. 59; 1982; pp. 625-643.					
EXAMINER /G. Nagesh Rao/ (06/23/2008)				DATE CONSIDERED 06/23/2008 <div style="text-align: right; font-weight: bold;">06/23/2008</div>			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /G.N.R./

Date: March 28, 2006